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ON Semiconductor®

FQT1N60C

N-Channel QFET® MOSFET

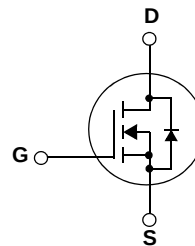
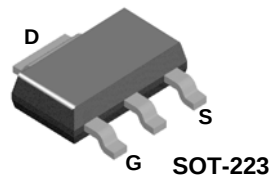
600V, 0.2 A, 11.5 Ω

Description

This N-Channel enhancement mode power MOSFET is produced using ON Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 0.2 A, 600 V, $R_{DS(on)}=9.3 \Omega$ (Typ.)@ $V_{GS}=10$ V, $I_D=0.1$ A
- Low Gate Charge (Typ. 4.8 nC)
- Low C_{rss} (Typ. 3.5 pF)
- 100% Avalanche Tested
- RoHS Compliant



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted*

Symbol	Parameter	FQT1N60C	Unit
V_{DSS}	Drain to Source Voltage	600	V
V_{GSS}	Gate to Source Voltage	± 30	V
I_D	Drain Current	-Continuous ($T_C = 25^\circ\text{C}$) -Continuous ($T_C = 100^\circ\text{C}$)	A
I_{DM}	Drain Current	- Pulsed (Note 1)	A
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	mJ
I_{AR}	Avalanche Current	(Note 1)	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	V/ns
P_D	Power Dissipation	($T_A = 25^\circ\text{C}$) - Derate above 25°C	W W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Min.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient*	-	60	$^\circ\text{C}/\text{W}$

* When mounted on the minimum pad size recommended (PCB Mount)

Package Marking and Ordering Information $T_C = 25^\circ\text{C}$ unless otherwise noted

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQT1N60C	FQT1N60C	SOT-223	330mm	12mm	4000

Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$, $T_J = 25^\circ\text{C}$	600	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, Referenced to 25°C	-	0.6	-	$V/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600\text{V}$, $V_{GS} = 0\text{V}$ $V_{DS} = 480\text{V}$, $T_C = 125^\circ\text{C}$	-	-	25 250	μA
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30\text{V}$, $V_{DS} = 0\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	2.0	-	4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}$, $I_D = 0.1\text{A}$	-	9.3	11.5	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{V}$, $I_D = 0.1\text{A}$ (Note 4)	-	0.75	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$	-	130	170	pF
C_{oss}	Output Capacitance		-	19	25	pF
C_{rss}	Reverse Transfer Capacitance		-	3.5	6	pF
Q_g	Total Gate Charge at 10V	$V_{DS} = 480\text{V}$, $I_D = 1\text{A}$ $V_{GS} = 10\text{V}$ (Note 4, 5)	-	4.8	6.2	nC
Q_{gs}	Gate to Source Gate Charge		-	0.7	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	2.7	-	nC

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 300\text{V}$, $I_D = 1\text{A}$ $R_G = 25\Omega$ (Note 4, 5)	-	7	24	ns
t_r	Turn-On Rise Time		-	21	52	ns
$t_{d(off)}$	Turn-Off Delay Time		-	13	36	ns
t_f	Turn-Off Fall Time		-	27	64	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current	-	-	0.2	A	
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	0.8	A	
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _{SD} = 0.2A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _{SD} = 1A	-	190	-	ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt = 100A/μs (Note 4)	-	0.53	-	μC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L = 59\text{mH}$, $I_{AS} = 1.1\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 0.2\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

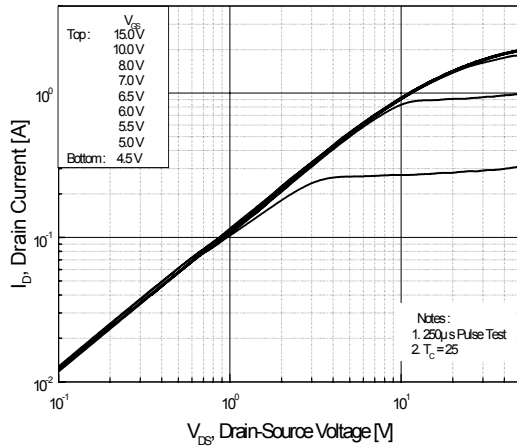


Figure 2. Transfer Characteristics

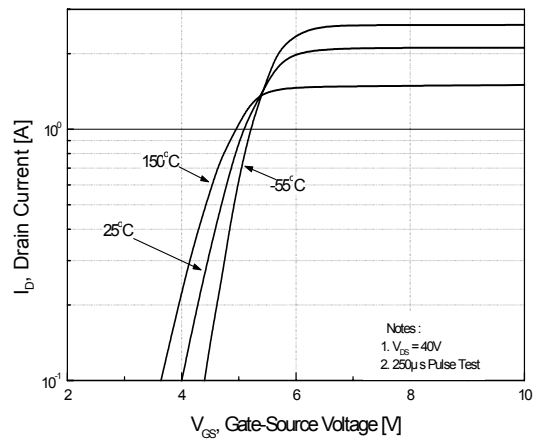


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

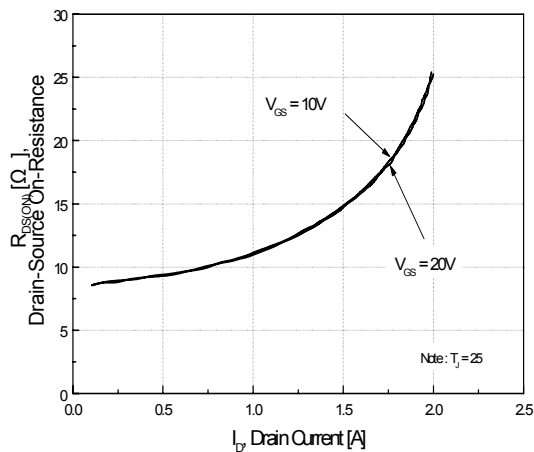


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

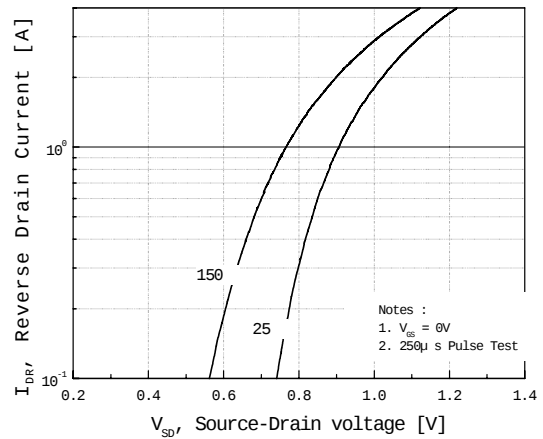


Figure 5. Capacitance Characteristics

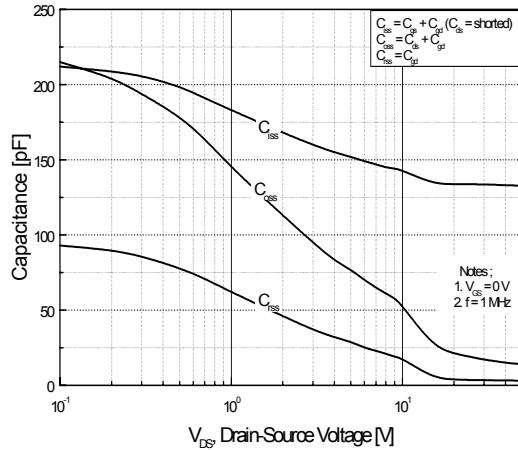
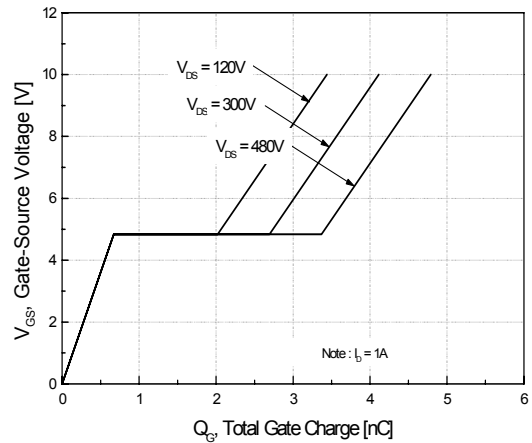


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

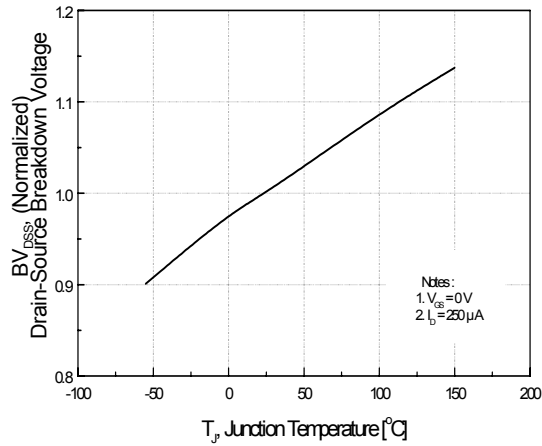


Figure 8. On-Resistance Variation vs. Temperature

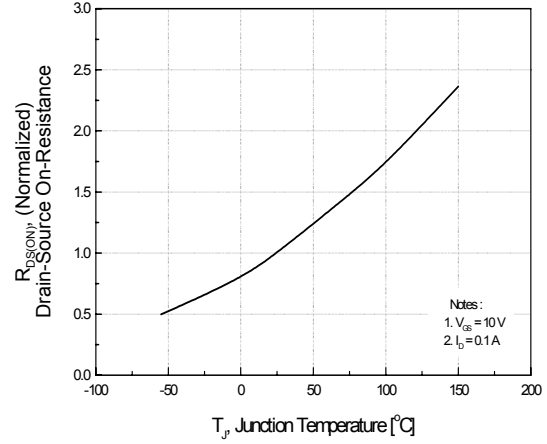


Figure 9. Maximum Safe Operating Area

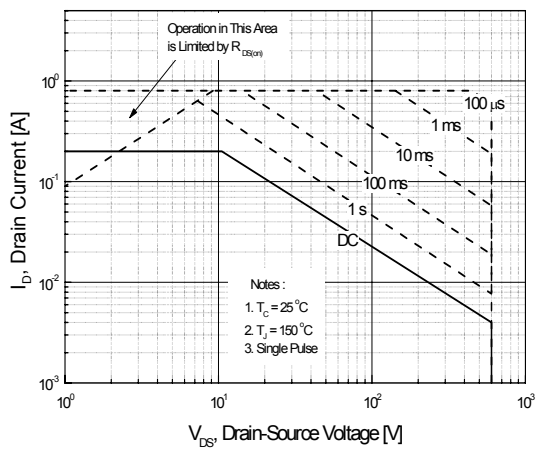


Figure 10. Maximum Drain Current vs. Case Temperature

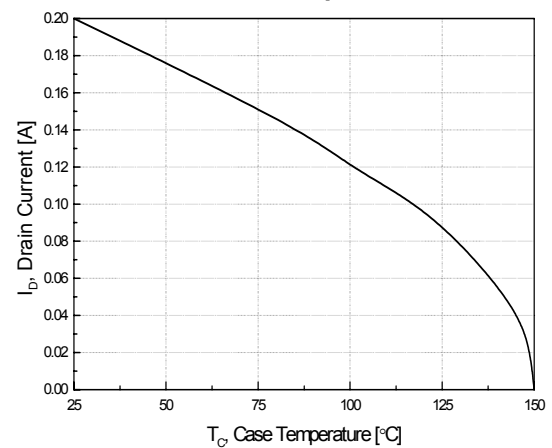
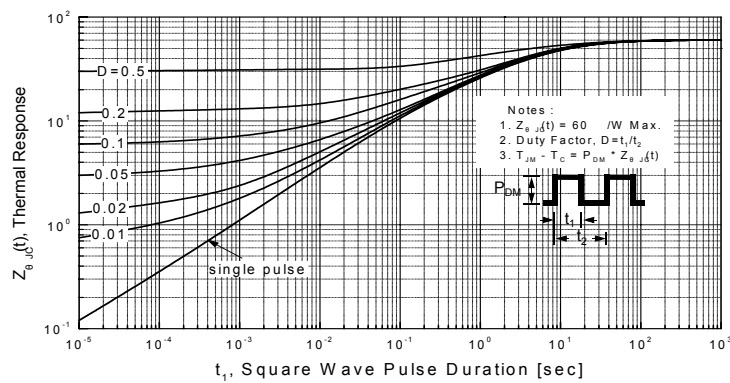
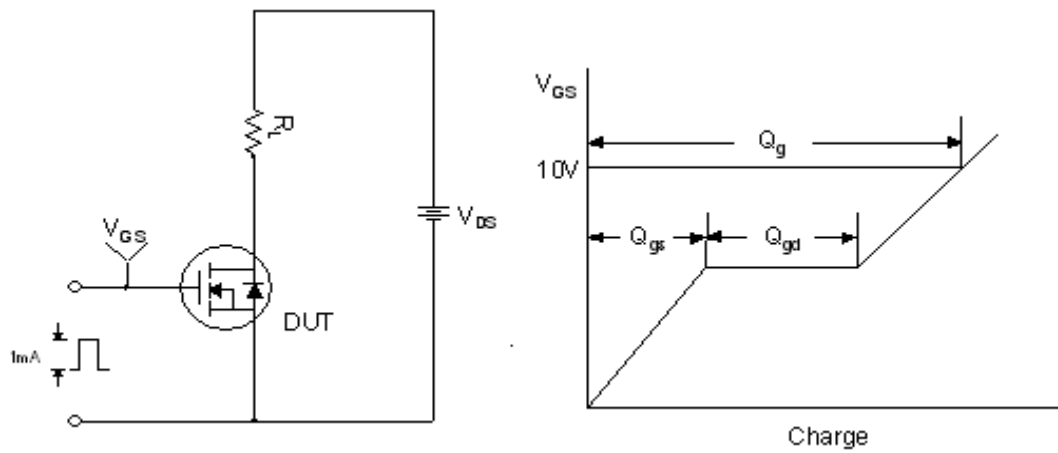


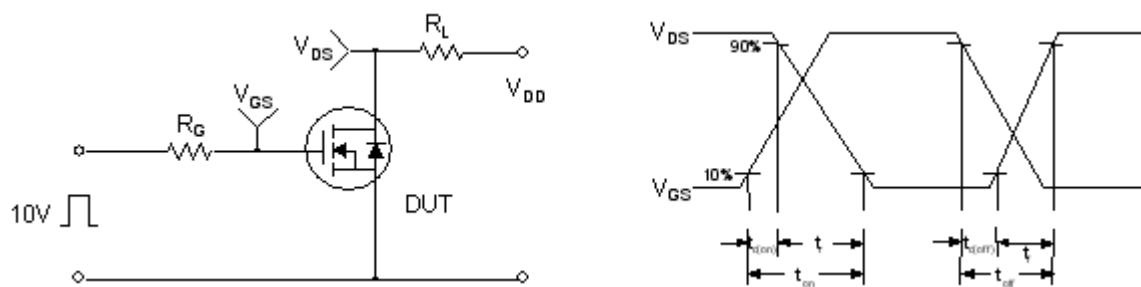
Figure 11. Transient Thermal Response Curve



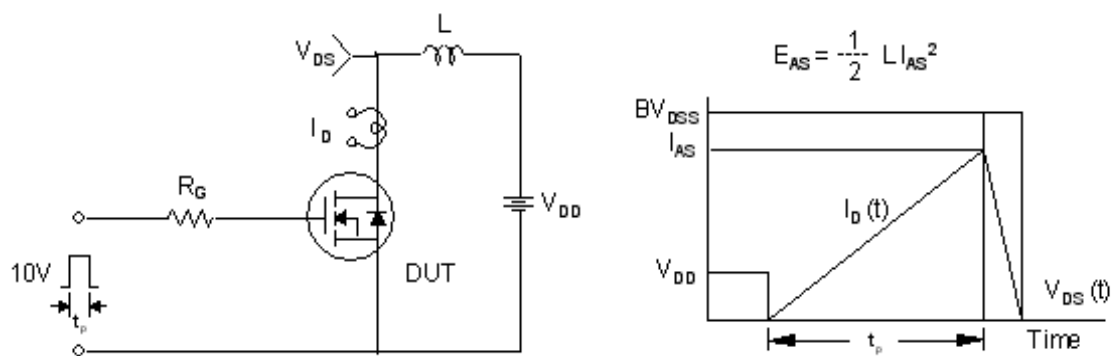
Gate Charge Test Circuit & Waveform



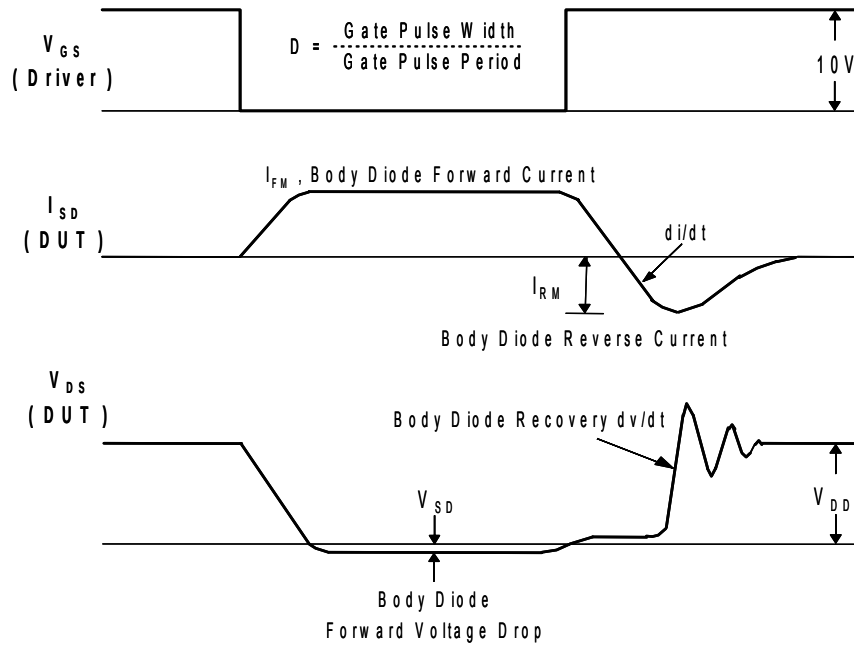
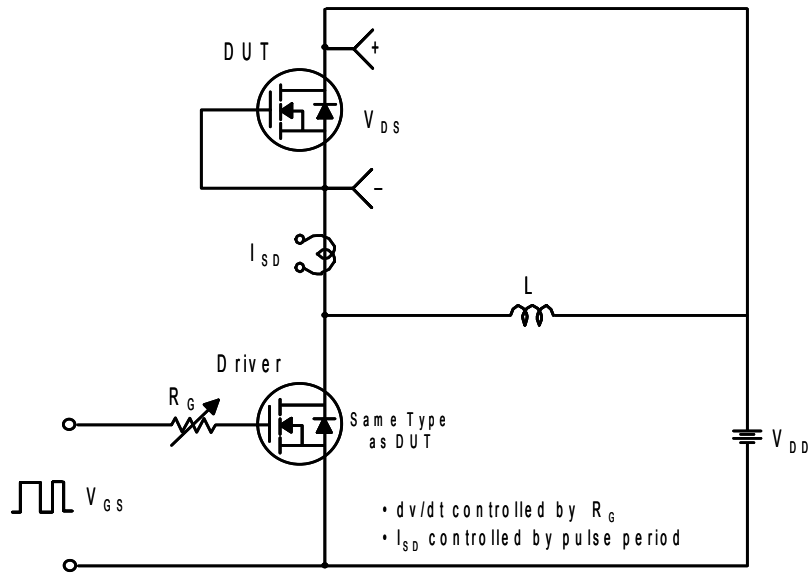
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms



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